

## Claims

- [c1] 1. A semiconductor device, comprising:
  - a first implant region having a first conductivity type;
  - and
  - a second implant region having a second conductivity type;
  - wherein said first and said second implant regions are self-aligned with respect to one another.
- [c2] 2. The semiconductor device of claim 1, wherein said first implant region is formed following a lithographic patterning step and said second implant region is formed following a non-lithographic, image reversal step.